OMB No. 0651-0011

# INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

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| Atty. Docket No. | 04329.2613 | Serial No. | Not Yet Assigned |
|---|---|---|---|
| Applicant | Katsuhiko HIEDA | | |
| Filing Date | July 30, 2001 | Group | |

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| Examiner | | Date Considered | 7 May 02 |
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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.